	Туре	Hits	Search Text	DBs	Time Stamp
1	BRS	34876	mosfet	USPAT; JPO	2002/08
2	BRS	26603	(semiconductor or die or chip or IC) and mosfet		2002/08 /15 18:52
3	BRS	22488	(semiconductor or die or chip or IC) and mosfet and (pad or electrode or contact or terminal)	USPAT; JPO	2002/08. /15 18:54
4	BRS	257	(semiconductor or die or chip or IC) and mosfet and (pad or electrode or contact or terminal) and power near module	1	2002/08 /15 18:55
5	BRS	137	(semiconductor or die or chip or IC) and mosfet and (pad or electrode or contact or terminal) and power near module and wire	USPAT; JPO	2002/08 /16 19:36
6	BRS	137	(semiconductor or die or chip or IC) and mosfet and (pad or electrode or contact or terminal) and power near module and wire	USPAT; JPO	2002/08 /16 15:13
7	BRS	728	((semiconductor or die or chip or IC) and mosfet and (pad or electrode or contact or terminal) and module and wire) not ((semiconductor or die or chip or IC) and mosfet and (pad or electrode or contact or terminal) and power near module and wire)	USPAT; JPO	2002/08 /16 15:14

	Туре	Hits	Search Text	DBs	Time Stamp
8	BRS	69	(semiconductor or die or chip or IC) and mosfet and (pad or electrode or contact or terminal) near (over or above) and module and wire	USPAT; JPO	2002/08 /16 15:59
9	BRS	1	"3893159".PN.	USPAT	2002/08 /16 15:56
10	BRS	1	"4578697".PN.	USPAT	2002/08 /16 15:56
11	BRS	1	"4589195".PN.	USPAT	2002/08 /16 15:57
12	BRS	1	"4988034".PN.	USPAT	2002/08 /16 15:57
13	BRS	1	"5306949".PN.	USPAT	2002/08 /16 15:57
14	BRS	1	"5324888".PN.	USPAT	2002/08 /16 15:59
15	BRS	7	"5306949"	USPAT; JPO	2002/08 /16 15:59
16	BRS	1	"3893159".PN.	USPAT	2002/08 /16 16:04
17	BRS	1	"4578697".PN.	USPAT	2002/08 /16 16:04
18	BRS	1	"4589195".PN.	USPAT	2002/08 /16 16:05
19	BRS	1	"4988034".PN.	USPAT	2002/08 /16 16:05
20	BRS	1	"4988034".PN.	USPAT	2002/08 /16 16:05
21	BRS	1	"5324888".PN.	USPAT	2002/08 /16 16:06

	Туре	Hits	Search Text	DBs	Time Stamp
22	BRS	75	(semiconductor or die or chip or IC) and mosfet and (pad or electrode or contact or terminal) and module and wire and switching near elements	USPAT; JPO	2002/08 /16 17:20
23	BRS	18	(semiconductor or die or chip or IC) and mosfet and (pad or electrode or contact or terminal) and power near module and wire and switching near elements	USPAT; JPO	2002/08 /16 18:13
24	BRS	1	(semiconductor or die or chip or IC) and mosfet and (pad or electrode or contact or terminal) near metal and power near module and wire and switching near elements	USPAT; JPO	2002/08 /16 18:08
25	BRS	865	(semiconductor or die or chip or IC) and mosfet and (pad or electrode or contact or terminal) and module and wire	USPAT; JPO	2002/08 /16 18:10
26	BRS	11	(semiconductor or die or chip or IC) and mosfet and (pad or electrode or contact or terminal) same (metal or copper) and power near module and wire and switching near elements	USPAT; JPO	2002/08 /16 18:17

	Туре	Hits	Search Text	DBs	Time Stamp
27	BRS	1	6353258.pn. and (semiconductor or die or chip or IC) and mosfet and (pad or electrode or contact or terminal) with (metal or copper) and power near module and wire and switching near elements	USPAT; JPO	2002/08 /16 19:20
28	BRS	7	6353258.pn. or 6417532.pn. or 6297549.pn. or 6272015.pn. or 6215679.pn. or 5926372.pn. or 2001237369.pn.	USPAT; JPO	2002/08 /16 19:21
29	BRS	34	(257/698 or 257/720 or 257/712 or 257/685 or 257/723 or 257/724) and (semiconductor or die or chip or IC) and mosfet and (pad or electrode or contact or terminal) and power near module and wire	EPO; JPO;	2002/08 /16 19:41
30	BRS	26	(257/690 or 257/691 or 257/692 or 257/784 or 257/107 or 257/213) and (semiconductor or die or chip or IC) and mosfet and (pad or electrode or contact or terminal) and power near module and wire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08 /16 19:42